

212 publications, h-index: 38 (Google Scholar)

2018

J. Spitaler and S.K. Estreicher, *Perspectives on the theory of defects*, chapter in “Density-Functional Theory and Beyond - Electronic Structure Theory Simulations of Materials and Molecules”, ed. C. Baldauf, V. Blum, and M. Scheffler (to be published)

C.M. Stanley and S.K. Estreicher, *Thermal properties of oxide layers in silicon: a first-principles study* (in preparation)

2017

S.K. Estreicher, *The beginning of wine and viticulture*

Physica Status Solidi c **14**, 1700008/1-5 (2017) <http://onlinelibrary.wiley.com/doi/10.1002/pssc.201700008/full>

C.M. Stanley and S.K. Estreicher, *Heat flow across an oxide layer in Si*,
Physica Status Solidi a **214**, 1700204/1-5 (2017)

T.M. Gibbons, D.J. Backlund, and S.K. Estreicher, *Cobalt-related defects in silicon*
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D.J. Backlund, T.M. Gibbons, and S.K. Estreicher, *Vanadium interactions in crystalline silicon*
Physical Review B **94**, 195210/1-6 (2016)

M.B. Bebek, C.M. Stanley, T.M. Gibbons, and S.K. Estreicher, *Temperature dependence of phonon-defect interactions: phonon scattering vs. phonon trapping*
Nature Scientific Reports **6**, 32150/1-10 (2016) DOI: 10.1038/srep32150 <http://rdcu.be/pLJe>

S.K. Estreicher, T.M. Gibbons, M.B. Bebek, and A. Cardona, *Heat flow and defects in semiconductors: beyond the phonon scattering assumption*
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T. M. Gibbons, M. B. Bebek, By. Kang, C.M. Stanley, and S. K. Estreicher, *Phonon-phonon interactions: first principles theory*
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By. Kang and S.K. Estreicher, *Thermal conductivity of Si nanowires: a first-principles analysis of the role of defects*
Physical Review B **89**, 155409/1-9 (2014)

A. Cavallini and S. K. Estreicher (**editors**), *Proc. 27th International Conference on Defects in Semiconductors*,
Journal of Applied Physics **115** (2014) (plenary and invited papers)

Preface: **Journal of Applied Physics** **115**, 011901 (2014)

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